

L Number	Hits	Search Text	DB	Time stamp
1	10104	(expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:06
8	652	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:06
15	6729	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) and (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:08
22	1447	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:08
29	4284	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) and (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:10
36	878	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:10
43	170	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:11
50	0	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?) and @ad19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:22
57	113	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?) and @ad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:22
64	57	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?) and @rlad<19971009	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:22
71	127	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?) and @ad<19971009) (((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) same (oxide dioxide dielectric insulat\$3 protect\$3 isolat\$3)) and (metallization metalization conduct\$3 wir\$3 interconnect\$3)) and (carbide SiC Si?sub.?) and @rlad<19971009)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:39

78	102	(anodiz\$3 anodization anodisation anodis\$3) near8 (carbide SiC Si?sub.?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:41
85	81	(anodiz\$3 anodization anodisation anodis\$3) near8 (((silicon Si) adj carbide) SiC Si?sub.?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:46
92	73	(anodiz\$3 anodization anodisation anodis\$3) near8 (((silicon Si) adj carbide) SiC SiC?sub.?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:47
99	6	((expand\$4 grow\$4 enlarg\$4 (increas\$4 near3 size)) near12 (pore porosity porousness)) and ((anodiz\$3 anodization anodisation anodis\$3) near8 (((silicon Si) adj carbide) SiC SiC?sub.??))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 12:47

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1	106029	((Si silicon) adj carbide) or SiC or SiC?sub.\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 16:55
8	43	(Si?sub.? adj C?sub.\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 16:57
9	43	(Si?sub.? adj C?sub.\$3 (Si?sub.? adj C?sub.\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 16:59
10	49476	(Si?sub.? adj C?sub.\$3 C?SUB.\$3(C.SUB.K1J))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 17:00
11	29	(Si?sub.? adj C?SUB.\$3(C.SUB.K1J))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 17:01
12	6170	((Si silicon) adj carbide) or SiC or SiC?sub.\$3) near15 (ILD PMD dielectric insulat\$4 isolat\$4 passivat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 17:02
19	7460	438/622-641.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 17:03
26	200	((Si silicon) adj carbide) or SiC or SiC?sub.\$3) near15 (ILD PMD dielectric insulat\$4 isolat\$4 passivat\$4) and 438/622-641.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 17:03